

SUBSTRATE PROCESSING METHOD, SUBSTRATE PROCESSING DEVICE, AND SOFTWARE

ABSTRACT

An etching method disclosed herein involves performing: a step for supplying, from a gas supply source to a gas supply path, each of a first etching gas and a second etching gas, the second etching gas including at least one selected from the group of an ammonia gas and an amine gas; a storage step for storing the first etching gas and the second etching gas in a reservoir provided in the gas supply path, and increasing an internal pressure of the reservoir; and a gas supply step for opening a valve provided downstream of the reservoir in the gas supply path, supplying the first etching gas and the second etching gas stored in the reservoir to a processing container in which a substrate is accommodated, and etching a first film formed on the substrate.

(Fig. 4)